

ABSTRACT OF THE DISCLOSURE

The method for fabricating a semiconductor device comprises the step of: forming a gate electrode on a semiconductor substrate with a gate insulation film formed therebetween; the step of implanting a dopant in the semiconductor substrate with the gate electrode as a mask to form a doped region in the semiconductor substrate; the step of forming a chemical oxide film on the doped region, which prevents the dopant implanted in the doped region from diffusing outside the semiconductor substrate; and the step of performing thermal processing for activating the dopant implanted in the doped region.